74AUP2G38

Low-power dual 2-input NAND gate; open drain

Rev. 11 — 31 July 2023

Product data sheet

1. General description

The 74AUP2G38 provides the dual 2-input NAND gate with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- · High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- ESD protection:
 - HBM: ANSI/ESDA/JEDEC JS-001 class 3A exceeds 5000 V
 - CDM: ANSI/ESDA/JEDEC JS-002 class C3 exceeds 1000 V
- · Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package								
	Temperature range	Name	Description	Version					
74AUP2G38DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
74AUP2G38GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1					
74AUP2G38GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116					
74AUP2G38GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203					

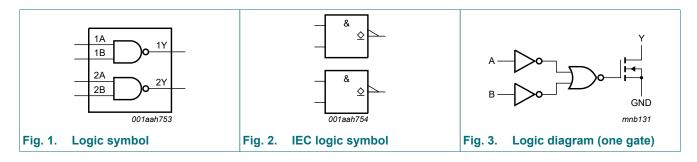
4. Marking

Table 2. Marking codes

Type number	Marking code[1]
74AUP2G38DC	a38
74AUP2G38GT	a38
74AUP2G38GN	аВ
74AUP2G38GS	аВ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

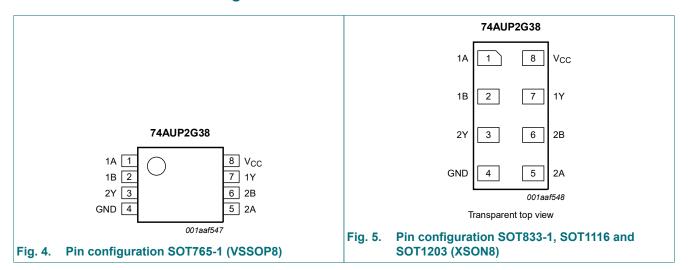
5. Functional diagram



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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state.

Input	Output	
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode [1]	-0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$ [2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions		Max	Unit
V _{CC}	supply voltage		8.0	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

^[2] For SOT765-1 (VSSOP8) package: Ptot derates linearly with 4.9 mW/K above 99 °C.

For SOT833-1 (XSON8) package: Ptot derates linearly with 3.1 mW/K above 68 °C.

For SOT1116 (XSON8) package: Ptot derates linearly with 4.2 mW/K above 90 °C.

For SOT1203 (XSON8) package: Ptot derates linearly with 3.6 mW/K above 81 °C.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C				1	
V _{IH}	HIGH-level input	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
voltage	voltage	V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
	V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V	
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
lį	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0 V$ to 3.6 V; $V_{CC} = 0 V$	-	-	±0.2	μA
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0 V$ to 3.6 V; $V_{CC} = 0 V$ to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μA
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF

Product data sheet

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
	voltage	V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
lį	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μA
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μA
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{IH}	HIGH-level input	V _{CC} = 0.8 V	0.75V _{CC}	-	-	V
	voltage	V _{CC} = 0.9 V to 1.95 V	0.70V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.25V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.30V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
l _l	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
ΔI _{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μA

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7.

Symbol	Parameter	Conditions	Ta	_{amb} = 25	°C	T _{amb} = -40 °C to +85 °C		T _{amb} = -40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	Min	Max	
C _L = 5 p	F									
t _{pd}	propagation	nA, nB to nY; see Fig. 6 [2]								
	delay	V _{CC} = 0.8 V	-	13.5	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	1.9	4.6	10.4	1.8	11.4	1.8	12.6	ns
		V _{CC} = 1.4 V to 1.6 V	1.5	3.3	6.5	1.4	7.4	1.4	8.2	ns
		V _{CC} = 1.65 V to 1.95 V	1.2	2.9	5.1	1.1	5.9	1.1	6.5	ns
		V _{CC} = 2.3 V to 2.7 V	1.0	2.2	3.8	0.9	4.5	0.9	4.9	ns
		V _{CC} = 3.0 V to 3.6 V	0.9	2.3	4.0	0.8	4.5	0.8	4.9	ns
C _L = 10	pF					'	1	1		
t _{pd}	propagation	nA, nB to nY; see Fig. 6 [2]								
	delay	V _{CC} = 0.8 V	-	16.3	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.3	5.6	12.3	2.1	13.7	2.1	15.1	ns
		V _{CC} = 1.4 V to 1.6 V	1.8	4.1	7.6	1.7	8.8	1.7	9.7	ns
		V _{CC} = 1.65 V to 1.95 V	1.6	3.8	6.1	1.4	7.1	1.4	7.8	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.9	4.6	1.2	5.4	1.2	5.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.3	3.2	5.7	1.1	6.4	1.1	7.0	ns
C _L = 15	pF					'			•	
t _{pd}	propagation	nA, nB to nY; see Fig. 6 [2]								
	delay	V _{CC} = 0.8 V	-	19.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	6.6	14.2	2.4	15.8	2.4	17.4	ns
		V _{CC} = 1.4 V to 1.6 V	2.1	4.8	8.7	1.9	10.1	1.9	11.1	ns
		V _{CC} = 1.65 V to 1.95 V	1.9	4.6	7.6	1.7	8.5	1.7	9.3	ns
		V _{CC} = 2.3 V to 2.7 V	1.6	3.6	5.6	1.5	6.3	1.5	6.9	ns
		V _{CC} = 3.0 V to 3.6 V	1.6	4.1	7.5	1.4	8.3	1.4	9.1	ns
C _L = 30	pF					'		<u>'</u>		
t _{pd}	propagation	nA, nB to nY; see Fig. 6 [2]								
	delay	V _{CC} = 0.8 V	-	27.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	9.5	19.5	3.2	21.8	3.2	24.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	7.0	11.5	2.6	13.6	2.6	15.0	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	7.0	12.1	2.3	13.3	2.3	14.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	5.4	8.9	2.1	9.9	2.1	10.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	6.5	12.7	2.1	13.9	2.1	15.3	ns

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Symbol	Parameter	Conditions	T,	_{amb} = 25 °				, = T _{amb} = +85 °C -40 °C to +125 °C		Unit
			Min	Typ [1]	Max	Min	Max	Min	Max	
$C_L = 5 p$	F, 10 pF, 15 p	F and 30 pF								
C _{PD}	power	$f = 1 \text{ MHz}$; $V_I = \text{GND to } V_{CC}[3]$								
	dissipation capacitance	V _{CC} = 0.8 V	-	0.6	-	-	-	-	-	pF
	Capacitario	V _{CC} = 1.1 V to 1.3 V	-	0.7	-	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	0.8	-	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	0.9	-	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	1.1	-	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	1.4	-	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PZL} and t_{PLZ} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

11.1. Waveforms and test circuit

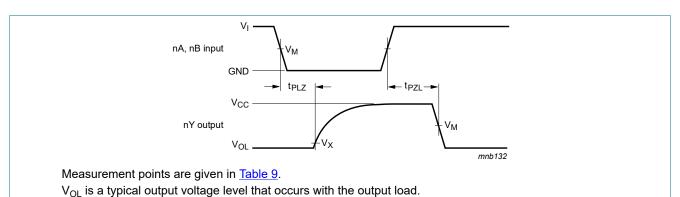
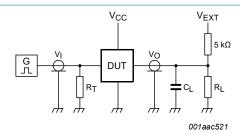


Fig. 6. The data input (nA, nB) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input			Output	
V _{CC}	V _M	V _I	t _r = t _f	V _M	V _X
0.8 V to 1.6 V	0.5V _{CC}	V _{CC}	≤ 3.0 ns	0.5V _{CC}	V _{OL} + 0.1 V
1.65 V to 2.7 V	0.5V _{CC}	V _{CC}	≤ 3.0 ns	0.5V _{CC}	V _{OL} + 0.15 V
3.0 V to 3.6 V	0.5V _{CC}	V _{CC}	≤ 3.0 ns	0.5V _{CC}	V _{OL} + 0.3 V

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Test data is given in Table 10.

Definitions for test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig. 7. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2V _{CC}

[1] For measuring enable and disable times R_L = 5 k Ω . For measuring propagation delays, set-up times, hold times and pulse width, R_L = 1 M Ω .

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12. Package outline

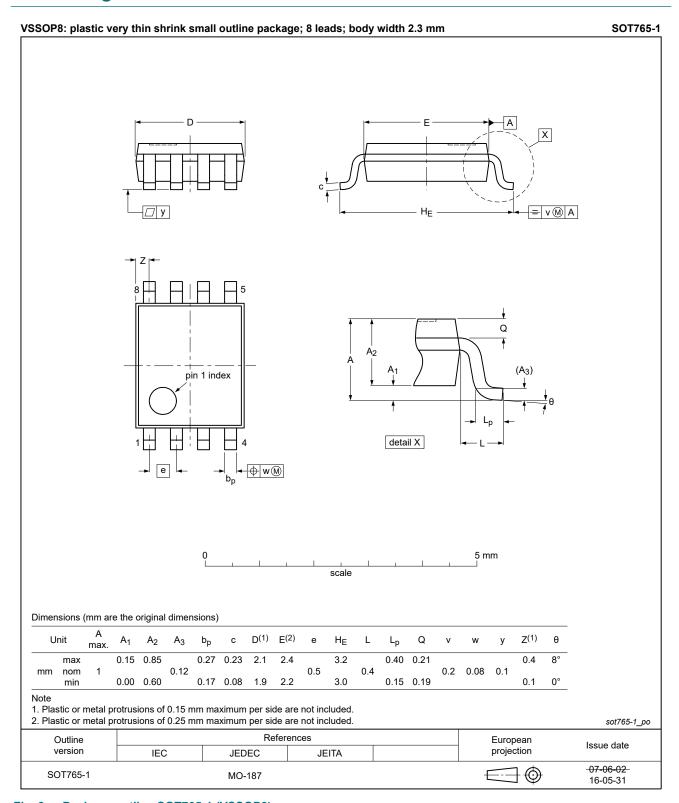


Fig. 8. Package outline SOT765-1 (VSSOP8)

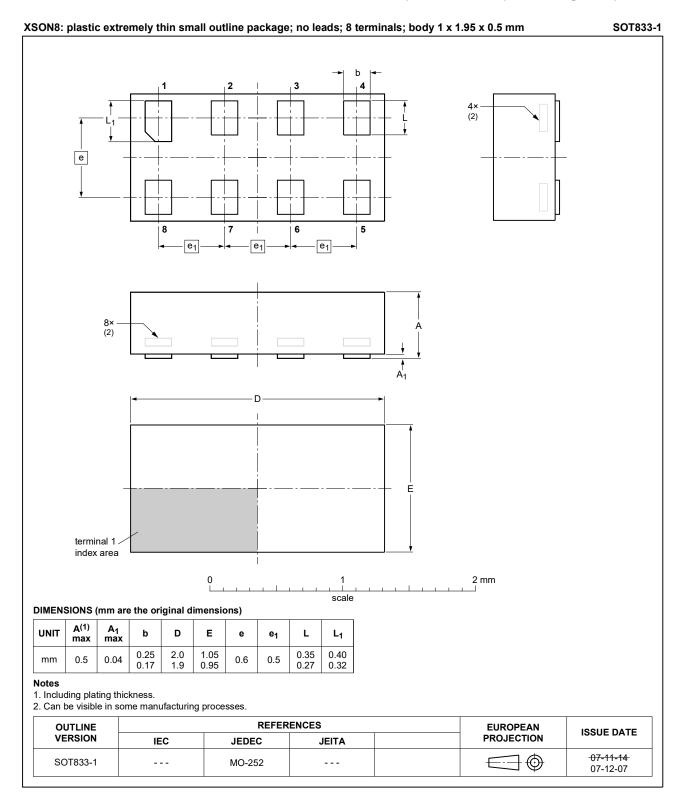


Fig. 9. Package outline SOT833-1 (XSON8)

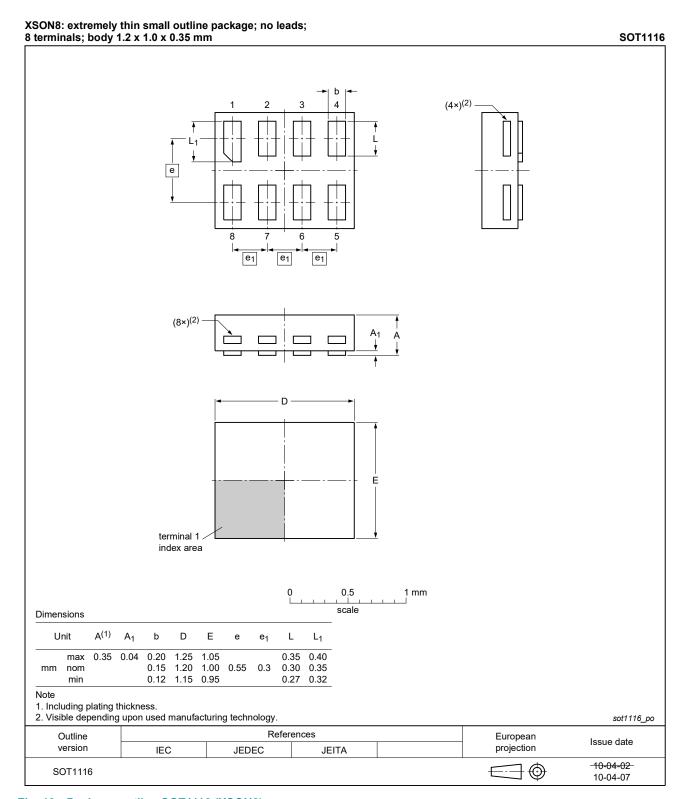


Fig. 10. Package outline SOT1116 (XSON8)

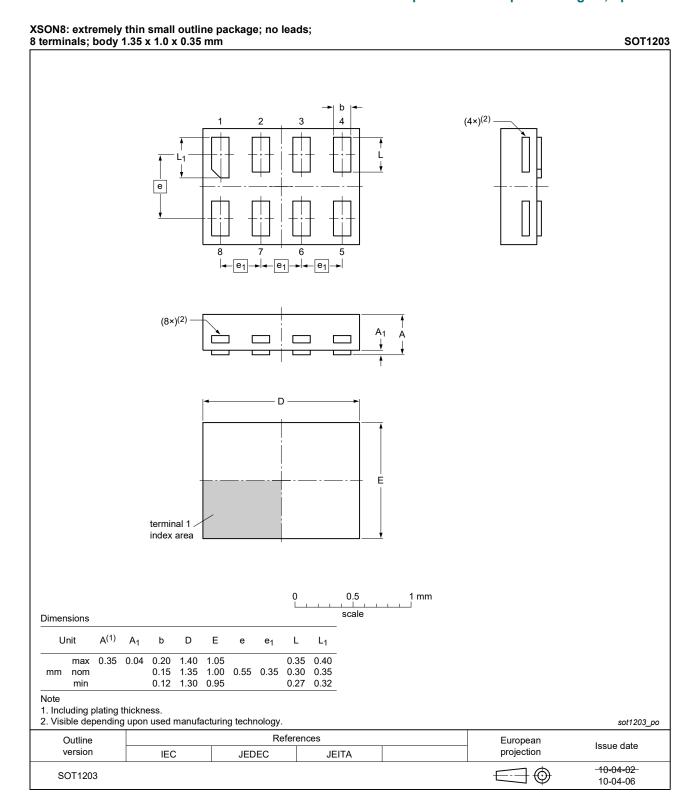


Fig. 11. Package outline SOT1203 (XSON8)

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G38 v.11	20230731	Product data sheet	-	74AUP2G38 v.10
Modifications:	<u>Section 2</u> : ESD specification updated according to the latest JEDEC standard.			
74AUP2G38 v.10	20201203	Product data sheet	-	74AUP2G38 v.9
Modifications:	 <u>Section 8</u>: Derating values for P_{tot} total power dissipation have been updated. Type numbers 74AUP2G38GF (SOT1089/XSON8) and 74AUP2G38GM (SOT902-2/XQFN8) removed. 			
74AUP2G38 v.9	20190326	Product data sheet	-	74AUP2G38 v.8
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Type numbers 74AUP2G38GD (SOT996-2) removed. Package outline drawing SOT765-1 (VSSOP8) updated. Package outline drawing SOT902-2 (XQFN8) updated. 			
74AUP2G38 v.8	20130211	Product data sheet	-	74AUP2G38 v.7
Modifications:	For type number 74AUP2G38GD XSON8U has changed to XSON8.			
74AUP2G38 v.7	20120605	Product data sheet	-	74AUP2G38 v.6
74AUP2G38 v.6	20111209	Product data sheet	-	74AUP2G38 v.5
74AUP2G38 v.5	20100923	Product data sheet	-	74AUP2G38 v.4
74AUP2G38 v.4	20091008	Product data sheet	-	74AUP2G38 v.3
74AUP2G38 v.3	20090616	Product data sheet	-	74AUP2G38 v.2
74AUP2G38 v.2	20080312	Product data sheet	-	74AUP2G38 v.1
74AUP2G38 v.1	20061016	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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